

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A magnetic non-volatile memory device provided with a magnetic shielding structure for suppressing the influence of external magnetic fields, said device characterized ~~by comprising~~ in that:

a magnetic shield layer made from a soft magnetic metal ~~on a surface of said device for suppressing penetration of magnetic flux into said device~~ is formed on a surface of said device for suppressing penetration of magnetic flux into said device, and

said magnetic shield layers are formed on a device surface at the mounting side of said device, and on a device surface opposite to said mounting side of said device.

2. (Canceled).

3. (Original) The magnetic non-volatile memory device according to claim1, said device characterized in that:
said magnetic shield layer is formed of a nano granular structure having a magnetic layer and a non-magnetic layer.

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4. (Original) The magnetic non-volatile memory device according to claim1,
said device characterized in that:

said magnetic shield layer has a composing element which is common to a
part of an element of various layers composing said device.

5. (Original) The magnetic non-volatile memory device according to claim1,
said device characterized in that:

a passivation film is formed on said magnetic shield layer.

Please add the following new claims:

6. (New) The magnetic non-volatile memory device according to claim1,
said device characterized in that:

said magnetic shield layers formed on a device surface at the mounting
side of said device, and a device surface opposite to said mounting side of said
device, are magnetically coupled with each other.

7. (New) The magnetic non-volatile memory device according to claim 4,
said device characterized in that:

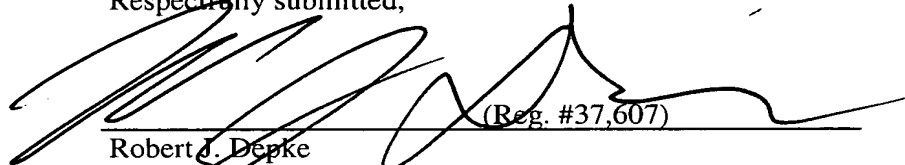
said composing element includes one selected from the group consisting of
Fe, Co, Pt, Mn, and Al.

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8. (New) A method for manufacturing a magnetic non-volatile memory device provided with a magnetic shielding structure for suppressing the influence of external magnetic fields, said method characterized in that:

various layers formed in said device, and a magnetic shield layer formed on a surface of said device for suppressing penetration of magnetic flux into said device are formed in a single sputtering chamber.

Respectfully submitted,



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